

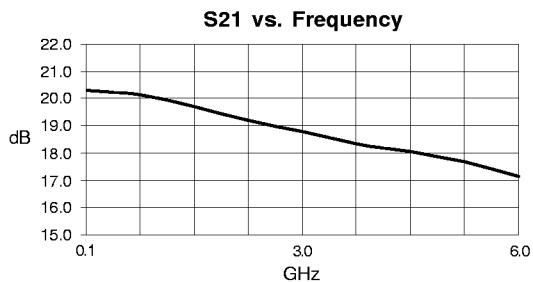


Product Description

Stanford Microdevices' NGA-589 is a high performance Gallium Arsenide Heterojunction Bipolar Transistor MMIC Amplifier. Designed with InGaP process technology for improved reliability, a Darlington configuration is utilized for broadband performance up to 6 GHz. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Typical output IP3 performance at 80mA is +38dBm at 900 MHz.

These unconditionally stable amplifiers provide up to 19dB of gain and 100mW of 1dB compressed power and requires only a single positive voltage supply. Only 2 DC-blocking capacitors, a bias resistor and an optional inductor are needed for operation.

This MMIC is an ideal choice for wireless applications such as cellular, PCS, CDPD, wireless data and SONET.



Electrical Specifications at Ta = 25C

Symbol	Parameters: Test Conditions: Id = 80mA, Z0 = 50 Ohms		Units	Min.	Typ.	Max.
GP	Power Gain	f = 0.1-2.0 GHz f = 2.0-3.0 GHz	dB dB		19.0 18.3	
GF	Gain Flatness Gain Flatness over any 100 MHz band	f = 0.1-3.0 GHz f = 0.1-3.0 GHz	dB dB		+/- 1.0 +/- 0.1	
P1dB	Output Power at 1dB Compression	f = 0.9 GHz f = 1.9 GHz	dBm dBm		19.0 18.5	
NF	Noise Figure	f = 0.1-3.0 GHz	dB		4.5	
IP3	Third Order Intercept Point	f = 0.9 GHz f = 1.9 GHz	dBm dBm		38.0 35.0	
VSWR	Input / Output	f = 0.1-3.0 GHz f = 3.0-6.0 GHz	-		1.5:1 1.7:1	
TD	Group Delay	f = 1.9 GHz	psec		90	
ISOL	Reverse Isolation	f = 0.1-6.0 GHz	dB		22.0	
VD	Device Voltage		V		5.0	

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Doc# EDS-100376 Rev. -

Preliminary

NGA-589

DC-6 GHz, Cascadable GaAs HBT MMIC Amplifier

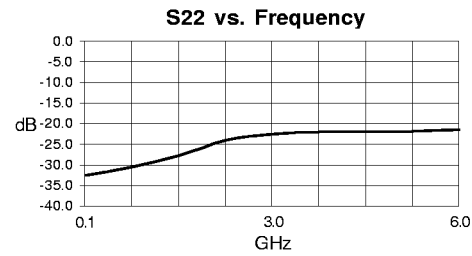
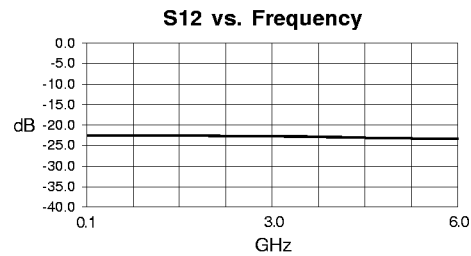
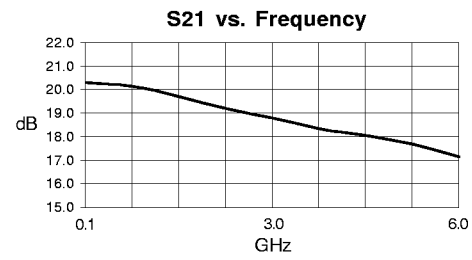
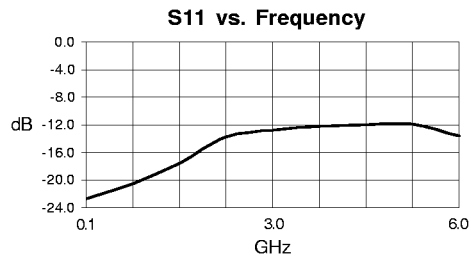


Product Features

- High Gain : 19dB at 2 GHz
- High Output IP3 : +38dBm at 900 MHz
- Cascadable 50ohm : 1.5:1 VSWR
- Patented GaAsHBT Technology
- Operates From Single Supply
- Low Thermal Resistance Package

Applications

- Cellular, PCS, CDPD
- Wireless Data, SONET

NGA-589 DC-6 GHz Cascadable MMIC Amplifier
Typical Performance at 25 °C ($V_{cc} = 5.0V$, $I_{cc} = 80mA$)

Typical S-Parameters $V_{cc} = 5.0V$, $I_{cc} = 80mA$

Freq GHz	S11	∠S11	S21	∠S21	S12	∠S12	S22	∠S22
.100	0.073	168	10.33	176	0.075	-23	0.023	162
.500	0.089	119	10.13	161	0.075	-23	0.031	126
.900	0.112	93	9.86	148	0.075	-23	0.040	101
1.00	0.119	90	9.85	145	0.075	-23	0.042	99
1.50	0.152	69	9.48	129	0.074	-23	0.054	85
2.00	0.183	51	9.07	114	0.074	-23	0.067	79
2.50	0.206	35	8.60	96	0.072	-23	0.075	70
3.00	0.225	21	8.27	84	0.071	-23	0.079	58
3.50	0.235	6	7.99	68	0.071	-23	0.081	42
4.00	0.244	-9	7.66	54	0.081	-23	0.082	36
4.50	0.240	-23	7.32	39	0.087	-23	0.087	37
5.00	0.208	-38	7.19	27	0.085	-24	0.085	41
5.50	0.179	-62	6.96	12	0.081	-24	0.081	43
6.00	0.185	-91	6.81	-3	0.058	-24	0.058	45



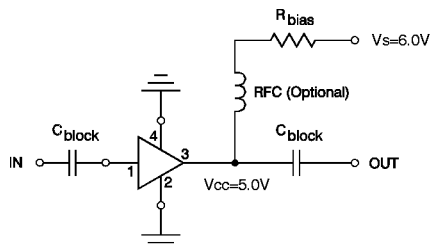
MTTF vs. Temperature @ I_{cc} = 80mA

Lead Temperature	MTTF (hrs)
+50C	>10,000,000
+80C	>1,000,000

Notes:

1. Operation of this device above any one of these parameters may cause permanent damage.

Recommended Bias Resistor Values						
Supply Voltage (Vs)	6V	7.5V	9V	12V	15V	20V
Rbias (Ohms) @ 80mA	12.5	31.5	50	88	125	188

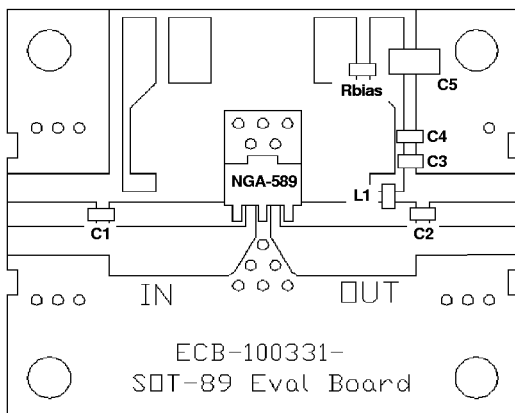


Typical Biasing Configuration
V_{cc}=5.0V, I_{cc}=80mA

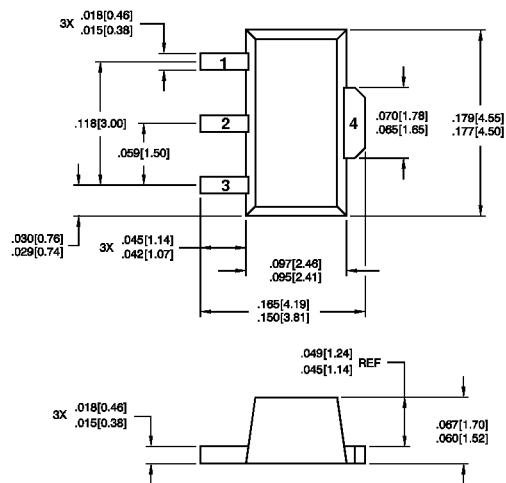
Pin Designation	
1	RF in
2	GND
3	RF out and Bias
4	GND

The data shown was taken on a 31mil thick FR-4 board with 1 ounce of copper on both sides.

1. Use 1 or 2 ounce copper, if possible.
2. Solder the copper pad on the backside of the device package to the ground plane.
3. Use a large ground pad area with many plated through-holes as shown.



Outline Drawing



DIMENSIONS ARE IN INCHES [MM]

Pin assignments shown for reference only, not marked on part